2SA1889

Silicon PNP Epitaxial

HITACHI

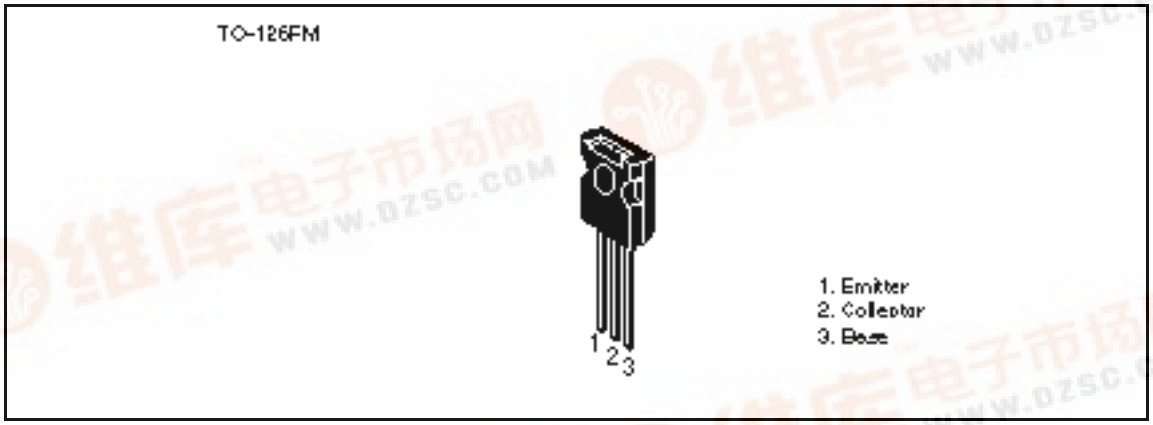
Application

High frequency amplifier

Features

- Excellent high frequency characteristics
  f_T = 300 MHz typ
- High voltage and low output capacitance
  V_{CEO} = –200 V, Cob = 5.0 pF typ
- Suitable for wide band video amplifier
- Complimentary pair of 2SC5024

Outline



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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	–200	V
Collector to emitter voltage	V_{CEO}	–200	V
Emitter to base voltage	V_{EBO}	–4	V
Collector current	I_C	–0.2	A
Collector peak current	$I_{C(peak)}$	–0.5	A
Collector power dissipation	P_C	1.4	W
Collector power dissipation	P_C*[1]	8	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–55 to +150	°C

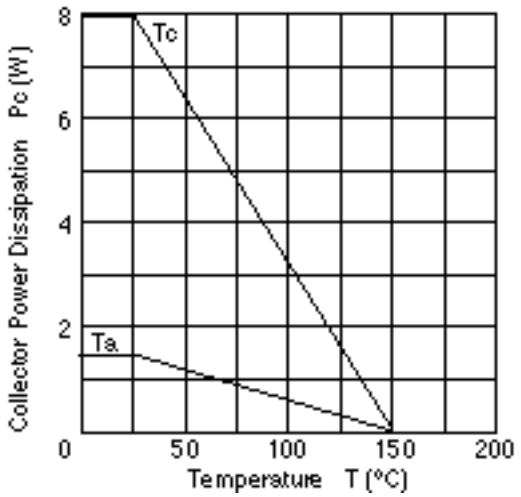
Note: 1. Value at T_C = 25°C.

Electrical Characteristics (Ta = 25°C)

Item		Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage		$V_{(BR)CBO}$	–200	—	—	V	I_C = –10 µA, I_E = 0
Collector to emitter breakdown voltage		$V_{(BR)CEO}$	–200	—	—	V	I_C = –1 mA, R_{BE} = ∞
Emitter to base breakdown voltage		$V_{(BR)EBO}$	–4	—	—	V	I_E = –10 µA, I_C = 0
Collector cutoff current		I_{CBO}	—	—	–10	µA	V_{CB} = –160 V, I_E = 0
DC current	2SA1889B	h_{FE}	60	—	120		V_{CE} = –5 V, I_C = –10 mA
transfer ratio	2SA1889C	h_{FE}	100	—	200		
Base to emitter voltage		V_{BE}	—	—	–1.0	V	V_{CE} = –5 V, I_C = –30 mA
Collector to emitter saturation voltage		$V_{CE(sat)}$	—	—	–1.0	V	I_C = –30 mA, I_B = –3 mA
Gain bandwidth product		f_T	200	300	—	MHz	V_{CE} = –20 V, I_C = –30 mA
Collector output capacitance		Cob	—	5.0	—	pF	V_{CB} = –30 V, I_E = 0, f = 1 MHz

See characteristic curves of 2SA1810.

Maximum Collector Power Dissipation Curve



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